

STARPOWER

SEMICONDUCTOR

IGBT

GD100MLX65L3S

650V/100A 3-level in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as 3-level-application.

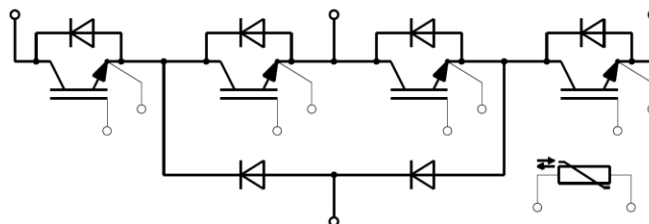
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 6 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175 °C
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Solar power
- UPS
- 3-level-application

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**T1-T4 IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	160	A
	@ $T_C=100^{\circ}\text{C}$	100	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	451	W

D1-D4 Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

D5,D6 Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

T1-T4 IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.45	1.90	V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.60			
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		1.70			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1.60\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.5	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			2.0		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		11.6		nF	
C_{res}	Reverse Transfer Capacitance				0.23		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.69		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=100\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		40		ns	
t_r	Rise Time			20		ns	
$t_{d(off)}$	Turn-Off Delay Time			192		ns	
t_f	Fall Time			40		ns	
E_{on}	Turn-On Switching Loss			0.44		mJ	
E_{off}	Turn-Off Switching Loss			2.00		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=300\text{V}, I_C=100\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		48		ns
t_r	Rise Time				24		ns
$t_{d(off)}$	Turn-Off Delay Time			208		ns	
t_f	Fall Time			52		ns	
E_{on}	Turn-On Switching Loss			0.68		mJ	
E_{off}	Turn-Off Switching Loss			2.68		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=100\text{A}, R_G=3.3\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			52		ns
t_r	Rise Time				24		ns
$t_{d(off)}$	Turn-Off Delay Time			216		ns	
t_f	Fall Time			60		ns	
E_{on}	Turn-On Switching Loss			0.78		mJ	
E_{off}	Turn-Off Switching Loss			2.80		mJ	
I_{SC}	SC Data		$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		500		A

D1-D4 Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.55	2.00	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.50		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.45		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		4.6		μC
I_{RM}	Peak Reverse Recovery Current			99		A
E_{rec}	Reverse Recovery Energy			1.32		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		8.6		μC
I_{RM}	Peak Reverse Recovery Current			121		A
E_{rec}	Reverse Recovery Energy			2.37		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		9.9		μC
I_{RM}	Peak Reverse Recovery Current			127		A
E_{rec}	Reverse Recovery Energy			2.64		mJ

D5,D6 Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.55	2.00	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.50		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.45		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		4.6		μC
I_{RM}	Peak Reverse Recovery Current			99		A
E_{rec}	Reverse Recovery Energy			1.32		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		8.6		μC
I_{RM}	Peak Reverse Recovery Current			121		A
E_{rec}	Reverse Recovery Energy			2.37		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=100\text{A},$ $-di/dt=3520\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		9.9		μC
I_{RM}	Peak Reverse Recovery Current			127		A
E_{rec}	Reverse Recovery Energy			2.64		mJ

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		15		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		2.00		$\text{m}\Omega$
R_{thJC}	Junction-to-Case (per T1-T4 IGBT)		0.302	0.332	K/W
	Junction-to-Case (per D1-D4 Diode)		0.538	0.592	
	Junction-to-Case (per D5,D6 Diode)		0.425	0.468	
R_{thCH}	Case-to-Sink (per T1-T4 IGBT)		0.283		K/W
	Case-to-Sink (per D1-D4 Diode)		0.506		
	Case-to-Sink (per D5,D6 Diode)		0.400		
	Case-to-Sink (per Module)		0.037		
F	Mounting Force Per Clamp	40		80	K/W
G	Weight of Module		39		g

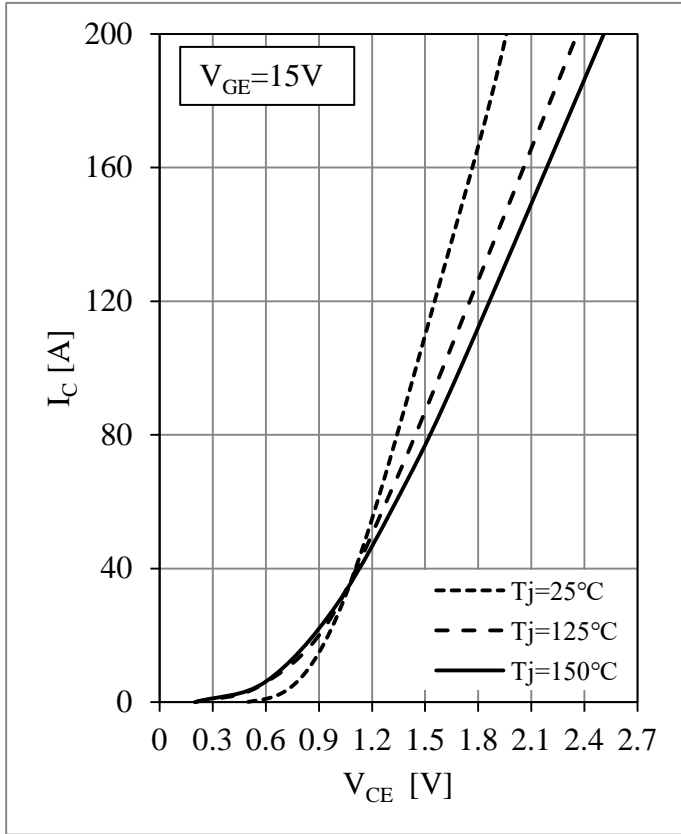


Fig 1. T1-T4 IGBT Output Characteristics

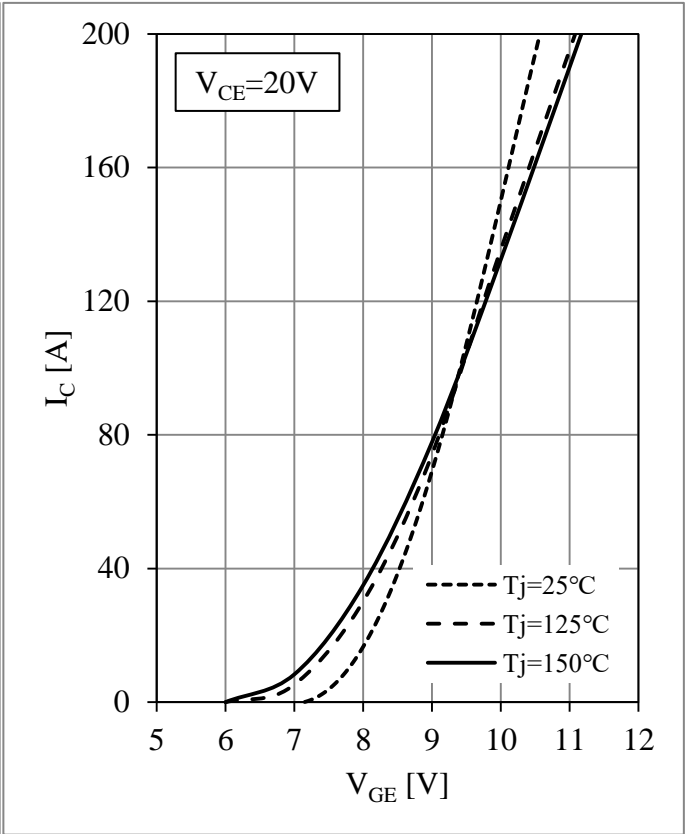


Fig 2. T1-T4 IGBT Transfer Characteristics

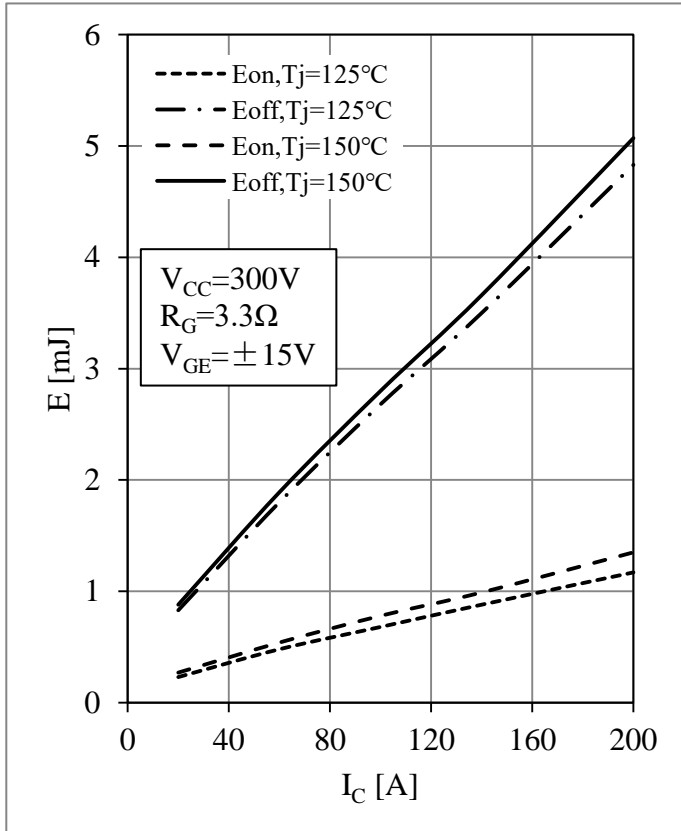


Fig 3. T1-T4 IGBT Switching Loss vs. I_C

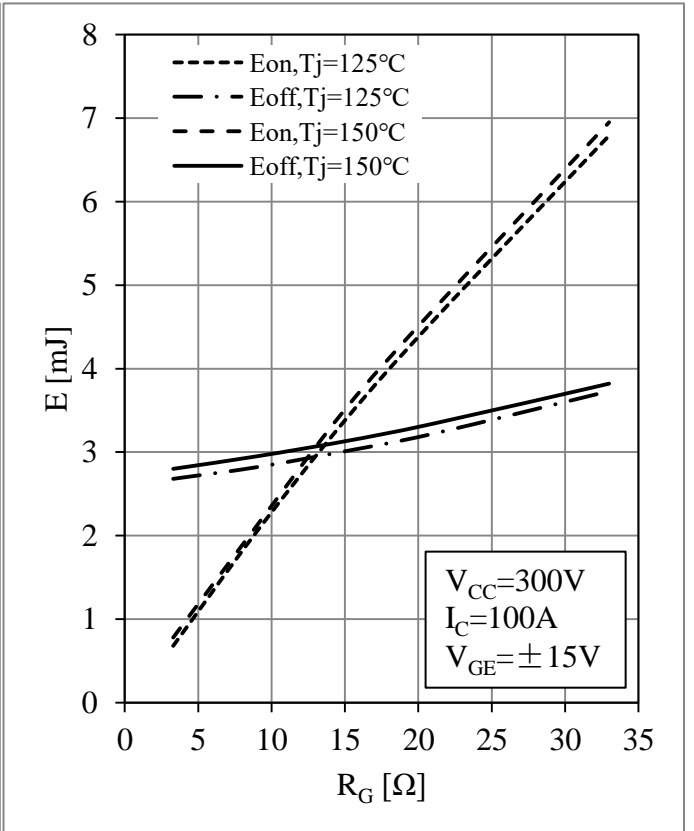


Fig 4. T1-T4 IGBT Switching Loss vs. R_G

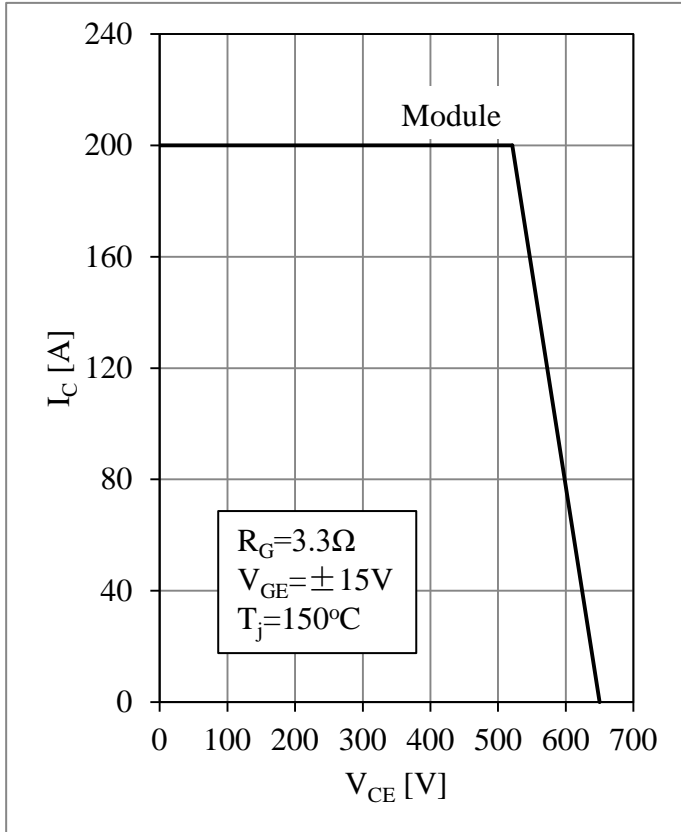


Fig 5. T1-T4 RBSOA

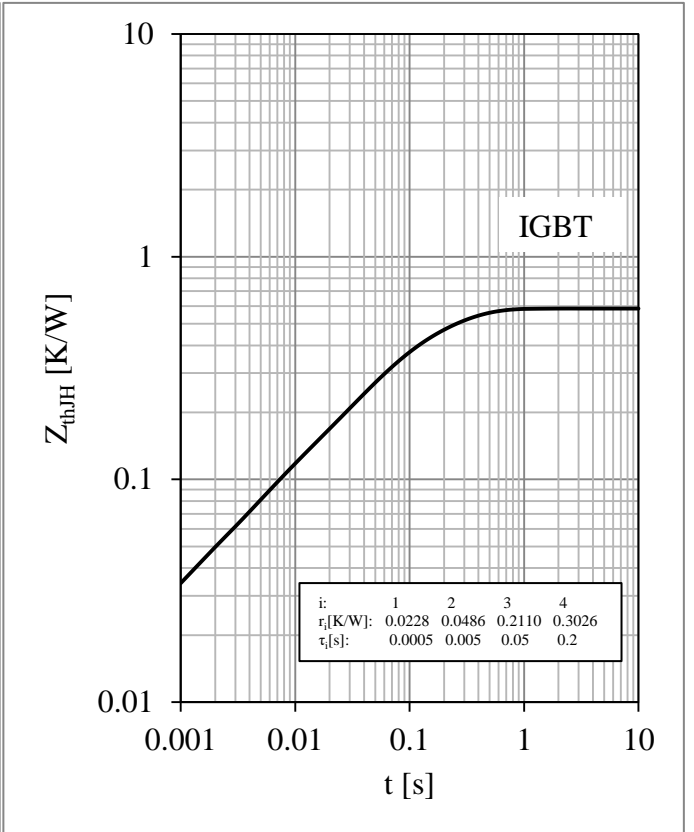


Fig 6. T1-T4 IGBT Transient Thermal Impedance

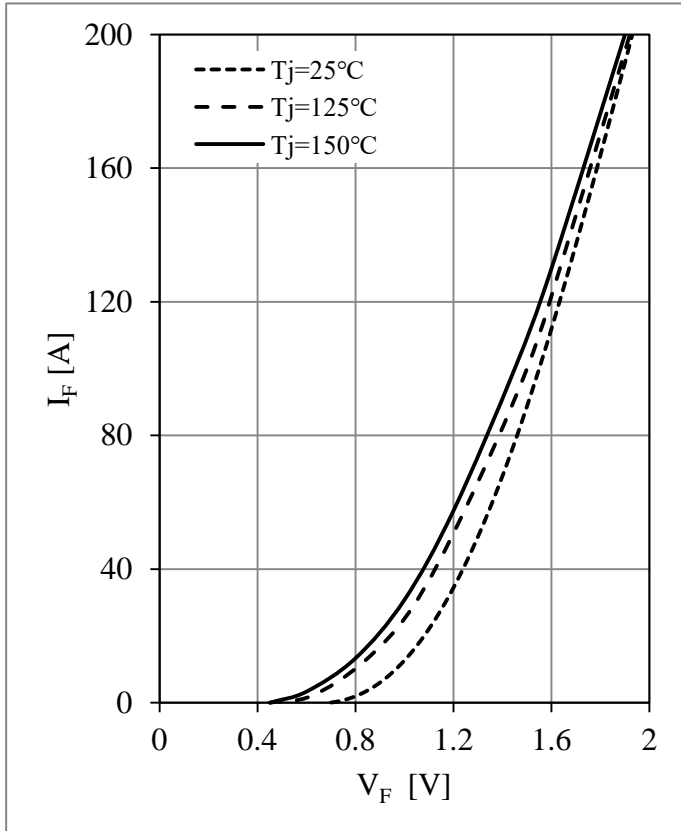


Fig 7. D1-D4 Diode Forward Characteristics

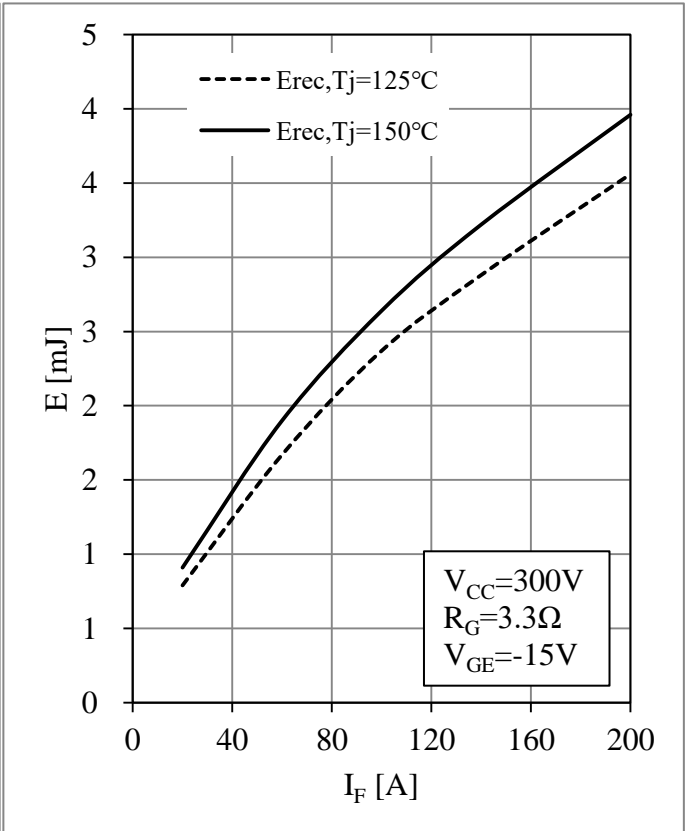


Fig 8. D1-D4 Diode Switching Loss vs. I_F

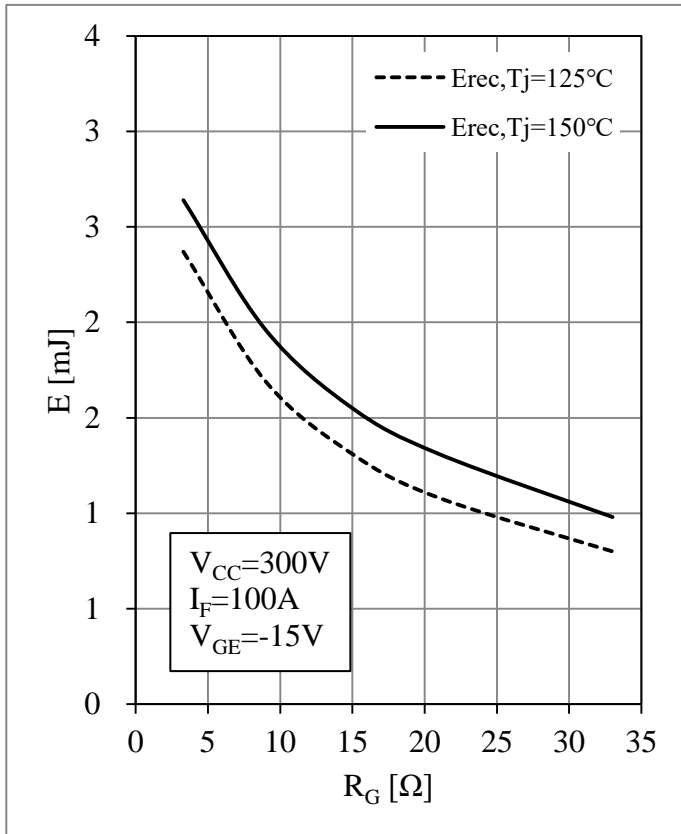


Fig 9. D1-D4 Diode Switching Loss vs. R_G

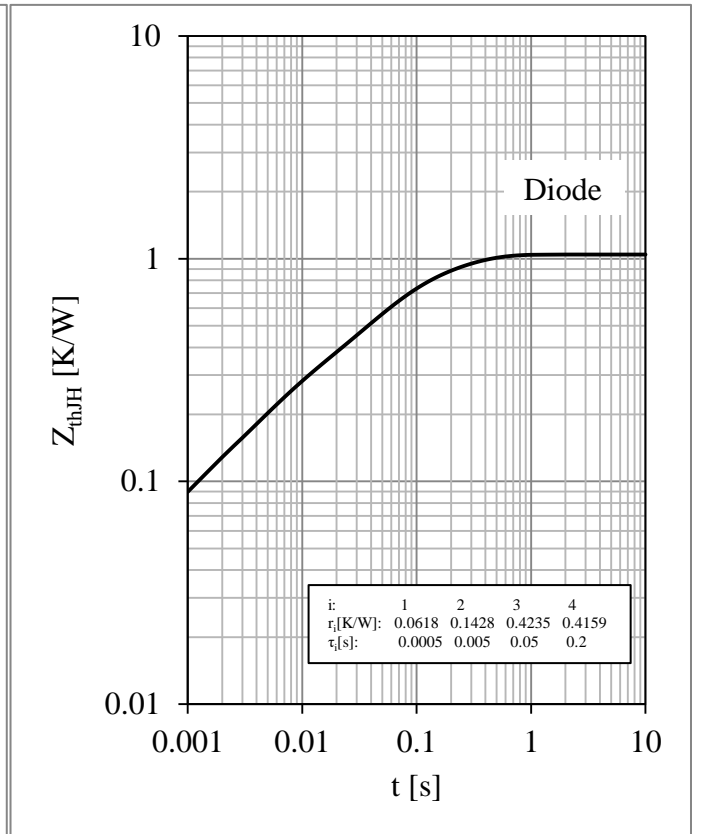


Fig 10. D1-D4 Diode Transient Thermal Impedance

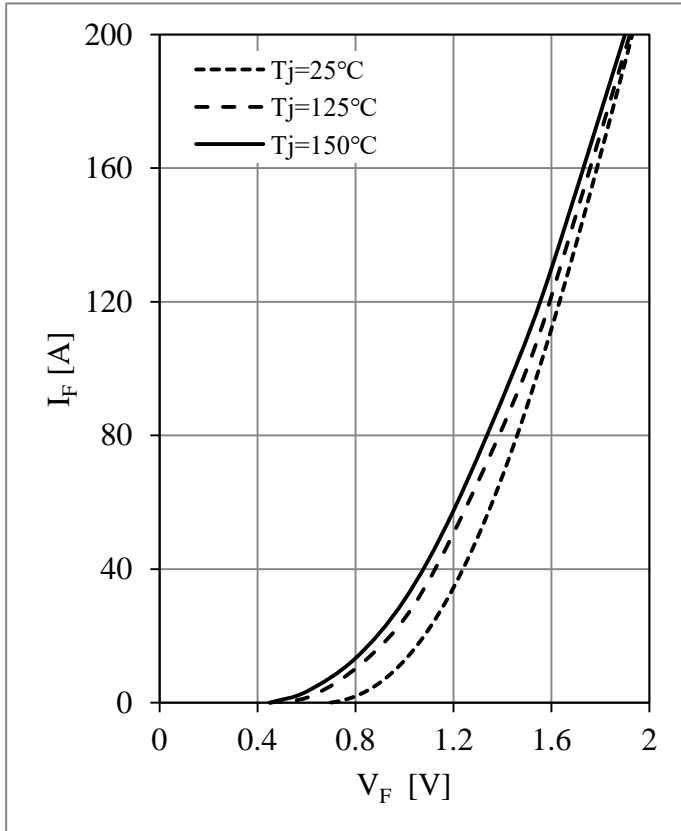


Fig 11. D5,D6 Diode Forward Characteristics

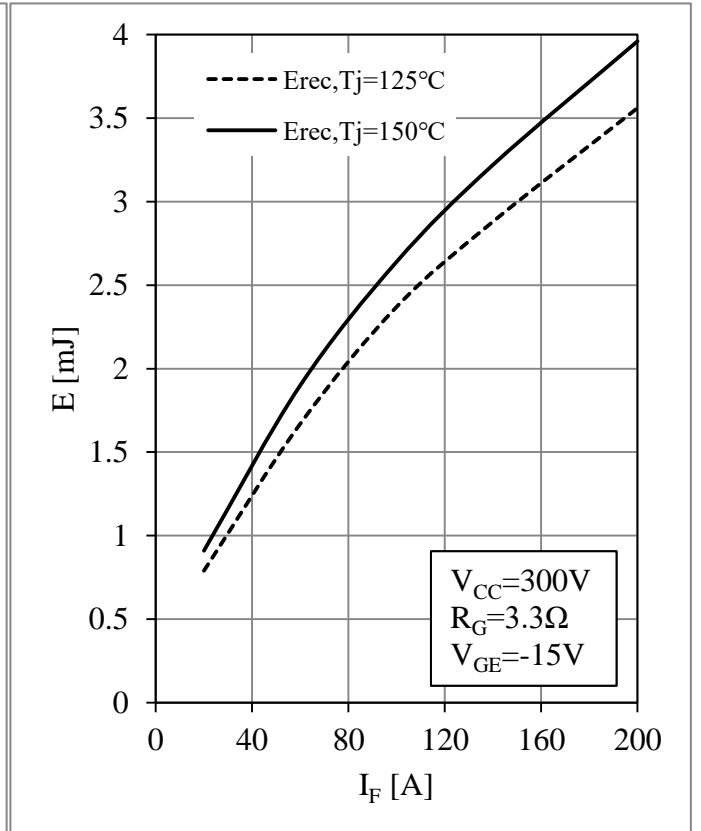


Fig 12. D5,D6 Diode Switching Loss vs. I_F

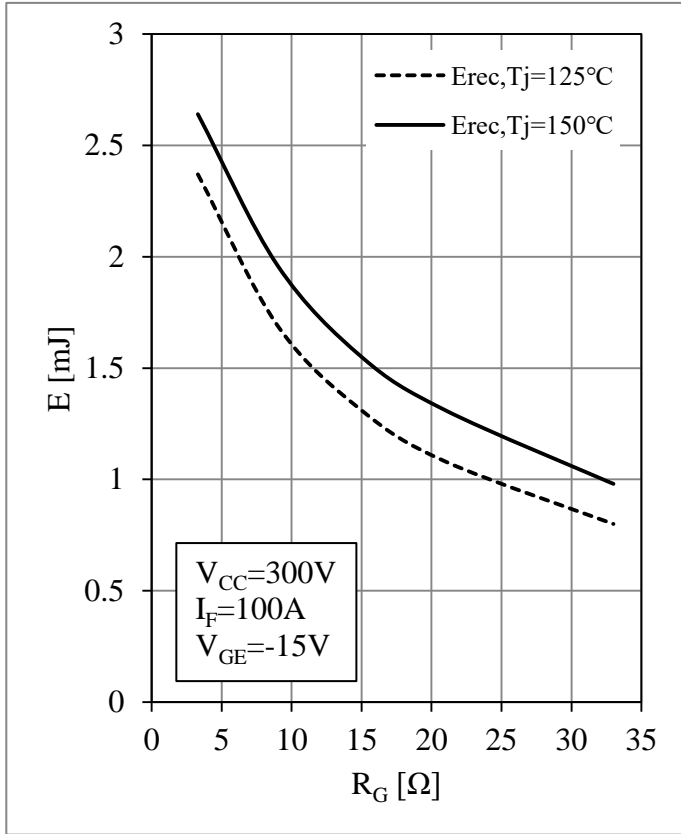


Fig 13. D5,D6 Diode Switching Loss vs. R_G

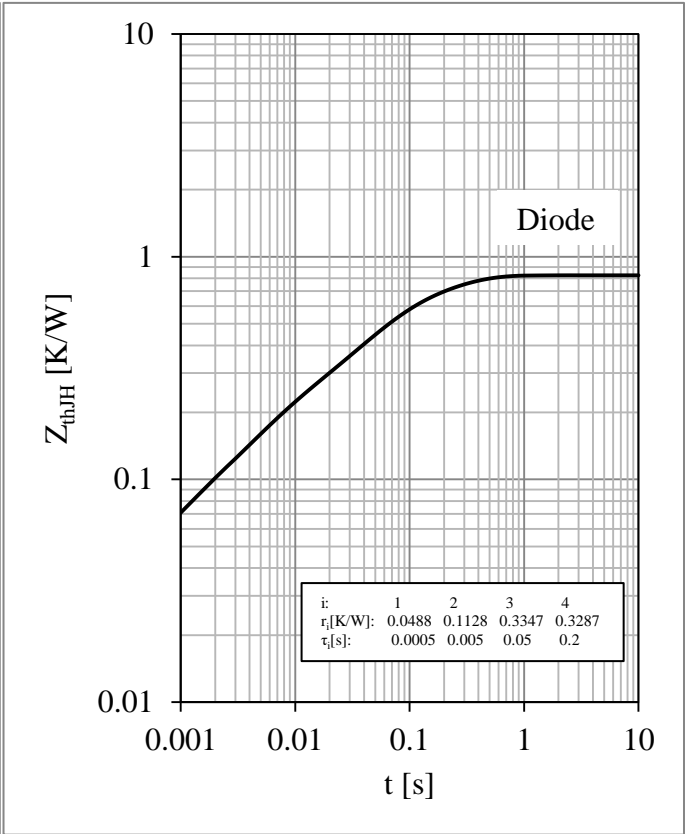


Fig 14. D5,D6 Diode Transient Thermal Impedance

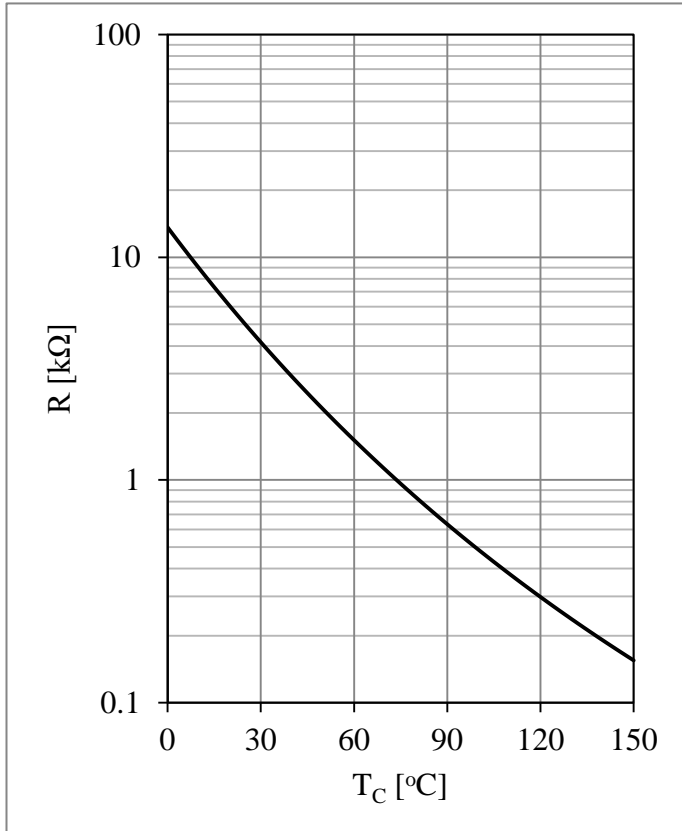
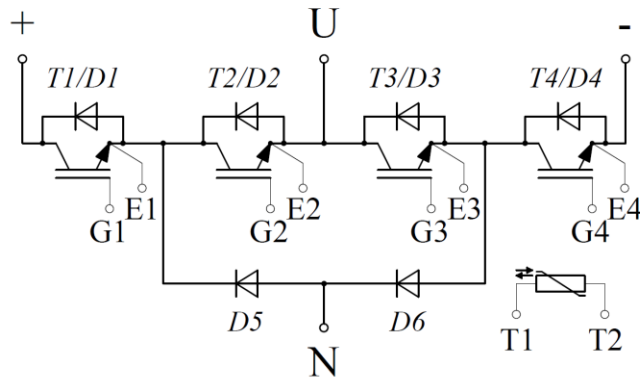


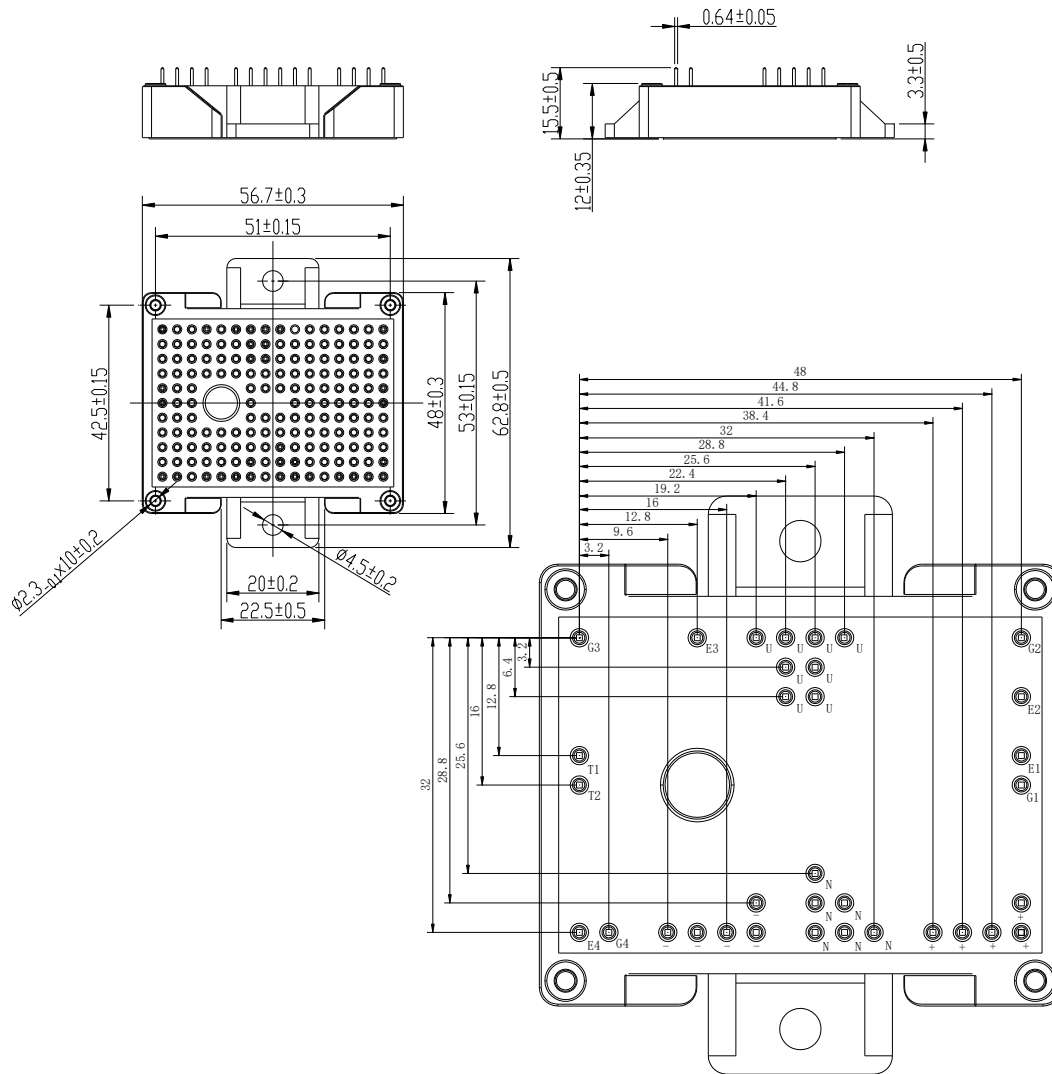
Fig 15. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



Pinpositions with tolerance $\oplus \ominus$

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